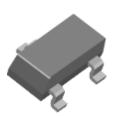
Analog Power AM1321P

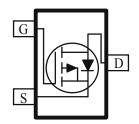
P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)}$ (OHM)	$I_{D}(A)$			
-20	$0.079 @V_{08} = -4.5V$	-1.7			
	$0.110 @V_{CS} = -2.5V$	-1.5			

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SC70-3 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter			Maximum Units		
Drain-Source Voltage		V_{DS}	-20	V	
Cate-Source Voltage			±8	V	
Continue Dair Communa	$T_A=25^{\circ}C$	T_	-1.7		
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	-1.4	Α	
Pulsed Drain Current ^b			-2.5		
Continuous Source Current (Diode Conduction) ^a		I_S	±0.28	Α	
D	T _A =25°C	D	0.34	W	
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	FD	0.22	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
N	$t \le 5 \sec$	D	375	OCAN 7		
Maximum Junction-to-Ambient ^a	Steady-State	R _{THJA}	430			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

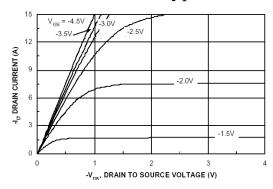
Donomoton	Cymbal	Test Conditions	Limits			TT *4	
Parameter	Symbol	1 est Conditions	Min	Тур	Max	Unit	
Static	-					-	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.4			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	A	
Zero Gate Voltage Drain Current	¹ DSS	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ} \text{C}$			-10	uA	
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-5			Α	
Drain-Source On-Resistance ^A		$V_{GS} = -4.5 \text{ V}, I_D = -1.7 \text{ A}$			79	mΩ	
Drain-Source On-Resistance	$r_{\mathrm{DS(on)}}$	$V_{GS} = -2.5 \text{ V}, I_D = -1.5 \text{ A}$			110) 111(2	
Forward Tranconductance ^A	g_{fs}	$V_{DS} = -5 \text{ V}, I_D = -1.25 \text{ A}$		9		S	
Diode Forward Voltage	V_{SD}	$I_S = -0.46 \text{ A}, V_{GS} = 0 \text{ V}$		-0.65		V	
Dynamic ^b							
Total Gate Charge	Qg	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		7.2			
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -1.7 \text{ A}$		1.7		пC	
Gate-Drain Charge	Q_{gd}	1 _D 1. / A		1.5			
Turn-On Delay Time	$t_{d(on)}$			10			
Rise Time	$t_{\rm r}$	$V_{DD} = -10 \text{ V}, I_L = -1 \text{ A},$		9		nc	
Turn-Off Delay Time	$t_{d(off)}$	V_{GEN} = -4.5 V, R_G = 6 Ω		27		ns	
Fall-Time	t_{f}			11		1	

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Repetitive rating, pulse width limited by junction temperature.

Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typical" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

Typical Electrical Characteristics



BAIN DORMALIZED

1.8

VGS=-2.0V

1.4

-2.5V

-3.5V

-4.5V

-4.5V

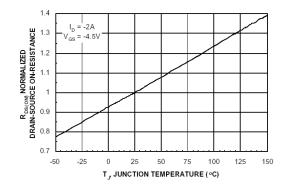
-4.5V

-4.5V

15.0, DRAIN CURRENT (A)

Figure 1. On-Region Characteristics

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage



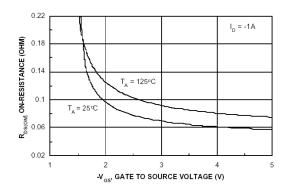
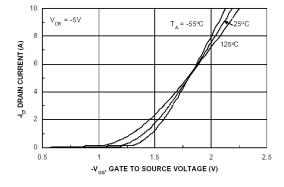


Figure 3. On-Resistance Variation with Temperature

Figure 4. On-Resistance Variation with Gate to Source Voltage



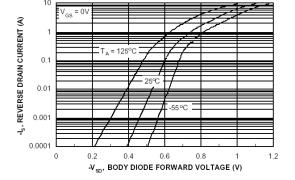
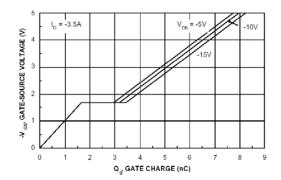


Figure 5. Transfer Characteristics

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics



1000 C_{ISS} C_{ISS}

Figure 7. Gate Charge Characteristic

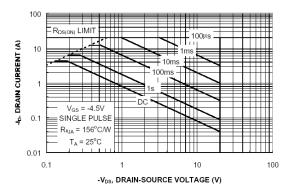


Figure 8. Capacitance Characteristic

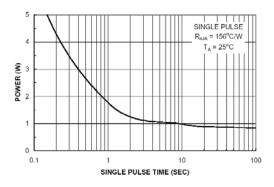


Figure 9. Maximum Safe Operating Area

Figure 10. Single Pulse Maximum Power
Dissipation



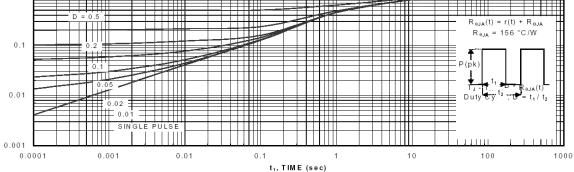
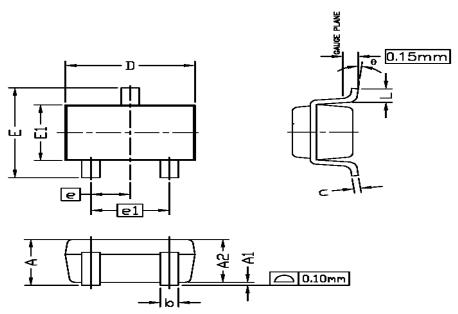


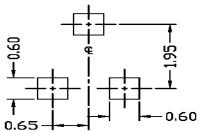
Figure 11. Transient Thermal Response Curve.

Package Information

SC70 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



TT	N	IT:	mn	-

SYMBOLS	DIMENSIONS IN MILLIMETERS DIMENSIONS IN INCHES			CHES			
SIMBULS	MIN	NOM	MAX	MIN	NOM	MAX	
Α			1.10			0.043	
A1	0.00		0.10	0.00		0.004	
A2	0.7	0.9	1.00	0.028	0.035	0.039	
ь	0.15		0.30	0.006		0.012	
c	0.08		0.22	0.003		0.009	
D	1.85	2.10	2,15	0.073	0.083	0.085	
E	1.80	2.30	2.40	0.071	0.091	0.094	
e	0.65 BSC			0.026 BSC			
el	1.30 BSC 0.051 BSC						
E 1	1.1	1.30	1.4	0.043	0.051	0.055	
L	0.26	0.36	0.46	0.010	0.014	0.018	
θ	0°	4°	80	O°	4°	8°	
					_		

NOTE

- 1. ALL DIMENSIONS ARE IN MILLMETERS.
- 2. DIMENSIONS ARE INCLUSIVE OF PLATING.
- 3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 3 MILS EACH.
- 4. DIE IS FACING UP FOR MOLD AND FACING DOWN FOR TRIM/FORM. ie: REVERSE TRIM/FORM.
- 5. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 6. CONTROLLING DIMENSION IS MILLIMETER.
- CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.